

ABSTRACT OF THE DISCLOSURE

The present invention provides an MR element bar that permits the fabrication of MR elements in which a variation in characteristics is suppressed, as well as an MR element bar exposure method and formation method enabling the  
5 fabrication of the MR element bar. The MR element bar exposure method according to the present invention comprises the steps of: detecting the positions of a plurality of alignment marks  $P_1$  to  $P_4$  formed on a wafer W; correcting  
10 an exposure position correction region R on the basis of the positions of detected alignment marks  $P_1'$  to  $P_4'$ ; and exposing a resist which is formed on the wafer W, wherein an MR element bar region B comprises a plurality of MR elements (patterns MRE) aligned in the longitudinal direction of the  
15 region B, and one exposure position correction region R is established for one MR element bar region B.